ELSEVIER

Thin Solid Films 276 (1996) 323–324

Thin Solid Films

Author Index of Volume 276

Abouliatim, A., 208
Adams, P.N., 299
Algueró, M., 212
Allegrini, M., 179
Amato, G., 51, 204
Anderle, M., 244
Andreu, R.C., 92
Andrianov, A.V., 235
Arens-Fischer, R., 21, 36, 40, 143, 231, 257
Arrand, H.F., 143
Asoka-Kumar, P., 310
Aylett, B.J., 253

Bachilo, E., 171
Baigent, D.R., 13
Banáš, S., 58
Bársony, I., 223
Bassas, J., 238
Baumbach, T., 69
Becker, P., 171
Bellet, D., 1, 69, 219
Belmont, O., 219
Ben-Chorin, M., 116, 120, 272
Benson, T.M., 143
Berger, M.G., 21, 36, 143, 231, 257
Berger, S., 108
Berlouis, L., 303
Bernardini, F., 261
Bertoni, S., 310
Bertran, E., 96
Binder, M., 65
Bisi, O., 244, 261
Boarino, L., 51, 204
Bock, W., 171
Bondarenko, V., 171, 296
Borisenko, V., 171
Borusík, O., 306
Bottani, C.E., 310
Brandt, M.S., 100
Brechet, Y., 219
Brunetto, N., 51, 204
Bsiesy, A., 130, 175
Bugiel, E., 92
Bullara, V., 204
Bustarret, E., 134
Buttard, D., 69

Cacialli, F., 13
Calcott, P.D.J., 112
Calliari, L., 244
Canham, L.T., 112, 143
Canillas, A., 96
Cantin, J.L., 32, 76, 92, 241
Cerofolini, G.F., 310
Cháb, V., 306
Chamarro, M., 92
Chvoj, Z., 306
Costa, J., 96
Cox, S.E., 299
Cox, T.I., 112
Cubeddu, R., 88
Cuevas, F., 212

Davison, M., 303
Deák, P., 290
Diener, J., 116, 120
Diligenti, A., 179
Dimova-Malinovska, D., 248, 318
Dittrich, Th., 183, 200, 216, 265, 287
Dolino, G., 1
Dörfel, I., 314
Dorigoni, L., 244, 261
Dorofeev, A., 171
Dyer, T.E., 306

Earwaker, L.G., 253
Ebert, M., 36
Edelmann, T., 65
Efros, Al.L., 120
Eggleston, J.M., 299
El-Kader, K.M.A., 306
Erostyák, J., 76

Faivre, C., 219
Fejfar, A., 187
Fernandez, J.F., 212
Ferrari, A., 168, 296
Fischer, T., 100
Flietner, H., 216
Forcey, K., 253
Fried, M., 223
Friend, R.H., 13
Frotscher, U., 36
Fuso, F., 179

Ganichev, S.D., 116
Gaponenko, N., 171
Gareeva, A.R., 287
Gaspard, F., 175
Gelloz, B., 175
Ghislotti, G., 88, 310
Giaddui, T., 253
Gippius, N.A., 120
Glück, O., 21, 231
Gnaser, H., 171
Goerigk, G., 65
Greef, R., 29
Greenham, N.C., 13
Grigoras, K., 191, 228
Grilli, E., 88
Grosman, A., 76
Grun, J.B., 55
Grüning, U., 151
Guha, S., 73
Guyader, P., 208
Guzzi, M., 88

Hadj Zoubir, N., 241
Hajnal, Z., 290
Halliday, D.P., 299
Halls, J.J.M., 13
Harding, I.S., 253
Hérino, R., 130
Hilbrich, S., 231, 257
Holland, E.R., 299
Holmes, A.B., 13
Hönerlage, B., 55
Hönlein, W., 138
Hory, M.A., 130
Hospodková, A., 55, 84
Houlton, M.R., 112
Hsu, K.Y.J., 147
Hwang, H.L., 147

Jaguiro, P., 168
Jalsovszky, G., 76
Jarašiūnas, K., 191
Joubert, P., 208

Kamenova, M., 248
Kamiya, A., 104
Kanemitsu, Y., 44
Kashkarov, P.K., 216, 265, 287
Katsouba, S., 168
Kavaliauskas, J., 228
Kazuchits, N., 171
Kissinger, W., 92
Kliefoth, K., 183
Knápek, P., 55
Knoll, B., 164
Koch, F., 100, 116, 120, 235
Kočka, J., 187, 306
Kohlová, V., 55, 58
Konstantinova, E.A., 216, 265
Kovalev, D., 120, 235
Kovalev, D.I., 116
Koynov, S., 314
Kozlowski, F., 73, 159, 164, 284
Krastev, V., 248, 318
Krištofik, J., 268
Krotkus, A., 228
Krüger, M., 21, 257
Kudrna, J., 58, 84
Kux, A., 120, 272

Laiho, R., 279
Lalic, N., 155
La Monica, S., 168, 296
Lang, W., 73, 159, 164, 284
Lau, H.W., 29
Lavallard, P., 293
Lazarouk, S., 168, 296
Lebib, S., 76
Lee, C.H., 147
Lehmann, V., 138, 151
Lérondel, G., 80
Leshok, A., 171
Lévy, R., 55
Lewerenz, H.J., 25
Ligeon, M., 130, 134
Linnros, J., 155
Lohner, T., 223
Loni, A., 112, 143
López-Villegas, J.M., 238
Luterová, K., 187
Lüth, H., 21, 143, 257
Lynn, K.G., 310

Madéore, F., 80
Maiello, G., 168, 296
Malý, P., 58, 84
Mareš, J.J., 268
Marinova, Ts., 248, 318
Marshall, J.M., 306
Martín, P., 212
Martinez, G., 47
Masini, G., 168, 296
Matveeva, A.B., 216
Mauckner, G., 65
Meda, L., 88, 310
Metzger, T.H., 65
Meulenkamp, E.A., 123
Miró, J., 290
Mizeikis, V., 191
Moniatte, J., 55
Monkman, A.P., 299
Morante, J.R., 96
Moratti, S.C., 13
Morazzani, V., 32
Morgenstern, T., 92
Muller, F., 80, 130, 175

Elsevier Science S.A.

Münder, H., 36, 143, 257
Mutti, P., 88

Nakao, S., 104
Nannini, A., 179
Nash, K.J., 112
Navarro, M., 238
Newey, J.P., 112
Nielsen, B., 310
Noor, U.M., 303

O'Donnell, K.P., 303
Oechsner, H., 171
Ortega, C., 32, 76
Ossicini, S., 244, 261
Oswald, J., 187, 268, 306

Pačebutas, V., 228
Pajot, B., 32
Papadimitriou, D., 238
Parisini, A., 51
Parker, G.J., 29
Parkhutik, V.P., 195
Pascual, E., 96
Pavesi, L., 244
Pavlov, A., 279
Peisl, J., 65
Pelant, I., 55, 58, 187, 306
Pellegrini, V., 179
Pennelli, G., 179
Penty, R.V., 123
Pershukevich, P., 296
Peter, L.M., 61, 123
Petrik, P., 223
Petrov, V.I., 287
Petrova-Koch, V., 100
Piel, J.P., 223
Pietryga, C., 36
Pifferi, A., 88
Polatoglou, H.M., 276
Polgár, O., 223
Polisski, G., 235

Rahbi, R., 32
Rappich, J., 25, 183, 200
Rauscher, S., 183, 200
Reeves, C., 112
Reisinger, H., 138
Richter, W., 36
Rikken, G.L.J.A., 47
Riley, D.J., 61, 123
Romestain, R., 80
Ronkel, F., 40
Rosen, M., 120
Rosenbauer, M., 32, 134
Rossi, A.M., 51
Rossow, U., 36
Roura, P., 96

Sailer, C., 164
Saitoh, K., 104
Samitier, J., 238
Sánchez, C., 212
Sauvain, E., 134
Schmidt, M., 314
Schoisswohl, M., 76, 92, 241
Schultze, J.W., 40
Schwarz, R., 314
Sedlačík, R., 187, 268
Sendova-Vassileva, M., 248, 318
Shcheglov, K., 100
Shimizu-Iwayama, T., 104
Sieber, I., 183, 200, 287, 314
Šimkiene, I., 191, 228
Simons, A.J., 112
Snow, P.A., 123
Spitzer, A., 138
Stehle, J.L., 223
Steiner, P., 73, 159, 164, 284
Stuchlík, J., 306
Subačius, L., 191
Sūdžius, M., 191
Suris, R.A., 293
Szeles, C., 310

Takeda, M., 104
Tamir, S., 108
Taroni, P., 88
Terao, Y., 104
The-Ha, H., 187
Theiß, W., 7, 231, 257
Thönissen, M., 21, 257
Tikhodeev, S.G., 120
Timoshenko, V.Yu., 183, 216, 265, 287
Tomasiunas, R., 55
Torricelli, A., 88
Trojánek, F., 58, 84
Troyanova, G., 171
Tzenov, N., 318

Ulrych, I., 306
Urban, I., 314
Uttamchandani, D., 303

Vazsonyi, E., 32, 76, 223
Vergnat, M., 241
Vial, J.C., 130
Vlachoudis, V., 276
Von Bardeleben, H.J., 32, 76, 92, 241
Vorozov, N., 171

Wagenseil, W., 284
Wendt, H., 138
White, I.H., 123
Wiedenhofer, A., 159, 284
Wielgosz, R.I., 61, 123
Willer, J., 138

Yeh, C.C., 147

Zanghieri, L., 88
Železný, V., 187
Zeman, J., 47
Zigone, M., 47

ELSEVIER

Thin Solid Films 276 (1996) 325–329

Thin Solid Films

Subject Index of Volume 276

Adsorption
adsorption-induced modification of spin and recombination centers in porous silicon, 265
Aluminium
visible light from aluminum–porous silicon Schottky junctions, 168
electroluminescence from aluminum–porous silicon reverse-biased Schottky diodes formed on the base of highly doped n-type polysilicon, 296
Ammonia
thermal nitridation of p-type porous silicon in ammonia, 32
Amorphous materials
temperature-dependent photoluminescence in porous amorphous silicon, 134
the influence of preparation conditions on the photoluminescence spectra of light-emitting Si prepared by laser pulse irradiation of a-Si:H, 306
Anisotropy
polarization of porous silicon photoluminescence: alignment and built-in anisotropy, 120
silicon needles in porous silicon, 293
Annealing
photoluminescence studies of light emission from silicon implanted and annealed SiO_2 layers, 88
on the structural origin of the photoluminescence in silicon powder produced in PECVD processes, 96
Anodic oxidation
influence of anodization time and current density on the photoluminescence of porous N–Si, 212
polarization memory induced by polarized light-assisted anodization of n-type Si, 235
Auger electron spectroscopy
Auger lineshape analysis of porous silicon: experiment and theory, 244

Capacitors
a novel capacitor technology based on porous silicon, 138
Carbon
visible luminescence from C-containing silicon oxide films, 318
Chemical vapour deposition
correlation between microstructure and photoluminescence of nanocrystalline silicon powder prepared by laser-induced CVD, 108
metallisation of porous silicon by chemical vapour infiltration and deposition, 253
microscopic characterization of microcrystalline silicon thin films, 314
Coatings
enhanced light absorption in anodically etched silicon wafers, 228
Cobalt
metallisation of porous silicon by chemical vapour infiltration and deposition, 253
Computer simulation
investigation of the non-radiative processes in porous silicon, 51
the luminescence transition in porous silicon: the nature of the electronic states, 261

Conductivity
electroluminescence from porous silicon using a conducting polyaniline contact, 299
Contacts
electrical characterization of metal Schottky contacts on luminescent porous silicon, 179

Deposition process
electrical contact to porous silicon by electrodeposition of iron, 40
strong 1.54 μm luminescence from erbium-doped porous silicon, 171
photoluminescence of laser-deposited porous silicon and its correlation with density of electronic states determined by scanning tunnelling microscopy, 279
Depth profiling
metallisation of porous silicon by chemical vapour infiltration and deposition, 253
Dielectric properties
polarization of porous silicon photoluminescence: alignment and built-in anisotropy, 120
the dielectric function of some low-dimensional Si and Ge structures, 276
Dielectrics
the dielectric function of porous silicon – how to obtain it and how to use it, 7
a novel capacitor technology based on porous silicon, 138
Diffusion
conduction in porous silicon contacted by a liquid phase, 175

Elastic properties
about the origin and the mechanisms involved in the cracking of highly porous silicon layers under capillary stresses, 219
Electrical properties and measurements
electrical characterization of metal Schottky contacts on luminescent porous silicon, 179
charge transport in porous silicon: considerations for achievement of efficient electroluminescence, 187
investigation of photoelectrical properties and carrier transport in porous silicon structures by the transient grating technique, 191
residual electrolyte as a factor influencing the electrical properties of porous silicon, 195
electroluminescence from aluminum–porous silicon reverse-biased Schottky diodes formed on the base of highly doped n-type polysilicon, 296
Electrochemistry
photo- and potential-controlled nanoporous silicon formation on n-Si(111): an in-situ FTIR Investigation, 25
high aspect ratio silicon pillars fabricated by electrochemical etching and oxidation of macroporous silicon, 29
electrical contact to porous silicon by electrodeposition of iron, 40
an in-situ method of monitoring the surface area of porous silicon, 61
mechanisms of luminescence tuning and quenching in porous silicon, 123
porous silicon multilayer optical waveguides, 143

Elsevier Science S.A.

characterization of porous silicon-on-insulator films prepared by anodic oxidation, 147
visible light from aluminum–porous silicon Schottky junctions, 168
strong 1.54 μm luminescence from erbium-doped porous silicon, 171
electronic properties of thin Au/nanoporous-Si/n-Si structures, 183
residual electrolyte as a factor influencing the electrical properties of porous silicon, 195
preparation of thin nanoporous silicon layers on n- and p-Si, 200
formation of porous silicon on patterned substrates, 257
dependence of PS photoluminescence on relative humidity, 268
Electronic devices
light-emitting and photoconductive diodes fabricated with conjugated polymers, 13
Electronic properties and measurements
the luminescence transition in porous silicon: the nature of the electronic states, 261
Electron microscopy
photoluminescence and chemical bonding in porous silicon layers—dependence on the P concentration in the Si substrate, 248
microscopic characterization of microcrystalline silicon thin films, 314
Electron spin resonance (ESR)
observation of (100) surfaces in p-type porous silicon by electron paramagnetic resonance, 241
Ellipsometry
investigation of different oxidation processes for porous silicon studied by spectroscopic ellipsometry, 36
characterization of different porous silicon structures by spectroscopic ellipsometry, 223
Erbium
strong 1.54 μm luminescence from erbium-doped porous silicon, 171
Etching
high aspect ratio silicon pillars fabricated by electrochemical etching and oxidation of macroporous silicon, 29
photoluminescence dynamics of porous silicon: picoseconds to milliseconds, 58
a novel capacitor technology based on porous silicon, 138
two-dimensional infrared photonic crystal based on macroporous silicon, 151
a porous silicon light-emitting diode with a high quantum efficiency during pulsed operation, 155
enhanced light absorption in anodically etched silicon wafers, 228
polarization memory induced by polarized light-assisted anodization of n-type Si, 235
formation of porous silicon on patterned substrates, 257
dependence of PS photoluminescence on relative humidity, 268
photo-assisted evolution of the photoluminescence spectrum of porous silicon immersed in hydrofluoric acid, 303

Fourier transform infrared spectroscopy
photo- and potential-controlled nanoporous silicon formation on n-Si(111): an in-situ FTIR Investigation, 25
on the origin of blue luminescence arising from atmospheric impregnation of oxidized porous silicon, 112

Germanium
mechanism of visible photoluminescence from oxidized silicon and germanium nanocrystallites, 44
defects and visible photoluminescence in porous $Si_{1-x}Ge_x$, 92
the dielectric function of some low-dimensional Si and Ge structures, 276
Growth mechanism
charge transport in porous silicon: considerations for achievement of efficient electroluminescence, 187
about the origin and the mechanisms involved in the cracking of highly porous silicon layers under capillary stresses, 219

Hydrocarbons
on the origin of blue luminescence arising from atmospheric impregnation of oxidized porous silicon, 112

Indium
influence of different metallic contacts on porous silicon electroluminescence, 159
time-resolved electroluminescence of porous silicon, 164
Infrared spectroscopy
stable and efficient cathodo- and photoluminescence from ultrathin porous silicon layers, 287
Interfaces
light scattering from porous silicon, 80
observation of (100) surfaces in p-type porous silicon by electron paramagnetic resonance, 241
Ion implantation
continuously tunable photoluminescence from Si^+-implanted and thermally annealed SiO_2 films, 100
visible photoluminescence from silicon nanocrystals formed in silicon dioxide by ion implantation and thermal processing, 104
characterization of different porous silicon structures by spectroscopic ellipsometry, 223
characterization of silicon-implanted SiO_2 layers using positron annihilation spectroscopy, 310

Laser irradiation
illumination-assisted formation of porous silicon, 21
the influence of preparation conditions on the photoluminescence spectra of light-emitting Si prepared by laser pulse irradiation of a-Si:H, 306
Light scattering
transient laser-induced grating spectroscopy in porous silicon, 55
excitation wavelength dependence of Raman and photoluminescence spectra of porous Si membranes, 73
light scattering from porous silicon, 80
Luminescence
the dielectric function of porous silicon – how to obtain it and how to use it, 7
thermal nitridation of p-type porous silicon in ammonia, 32
luminescence and Raman scattering from porous silicon under high hydrostatic pressure: a test for the present models of luminescence, 47
investigation of the non-radiative processes in porous silicon, 51
photoluminescence dynamics of porous silicon: picoseconds to milliseconds, 58
an in-situ method of monitoring the surface area of porous silicon, 61
excitation wavelength dependence of Raman and photoluminescence spectra of porous Si membranes, 73
photoluminescence studies of light emission from silicon implanted and annealed SiO_2 layers, 88
defects and visible photoluminescence in porous $Si_{1-x}Ge_x$, 92
on the structural origin of the photoluminescence in silicon powder produced in PECVD processes, 96
continuously tunable photoluminescence from Si^+-implanted and thermally annealed SiO_2 films, 100
visible photoluminescence from silicon nanocrystals formed in silicon dioxide by ion implantation and thermal processing, 104
on the origin of blue luminescence arising from atmospheric impregnation of oxidized porous silicon, 112
excitation of the porous silicon photoluminescence by a multiphoton vibronic process, 116
polarization of porous silicon photoluminescence: alignment and built-in anisotropy, 120
mechanisms of luminescence tuning and quenching in porous silicon, 123
investigation of the quenching mechanisms of the porous silicon luminescence, 130

temperature-dependent photoluminescence in porous amorphous silicon, 134
a porous silicon light-emitting diode with a high quantum efficiency during pulsed operation, 155
influence of different metallic contacts on porous silicon electroluminescence, 159
time-resolved electroluminescence of porous silicon, 164
strong 1.54 μm luminescence from erbium-doped porous silicon, 171
electrical characterization of metal Schottky contacts on luminescent porous silicon, 179
charge transport in porous silicon: considerations for achievement of efficient electroluminescence, 187
drying of porous silicon: a Raman, electron microscopy, and photoluminescence study, 204
effect of light intensity on photoluminescence properties of n-type porous silicon, 208
influence of anodization time and current density on the photoluminescence of porous N–Si, 212
influence of photoluminescence and trapping on the photovoltage at the por-Si/p-Si structure, 216
the influence of the doping level on the optical properties of porous silicon, 231
polarization memory induced by polarized light-assisted anodization of n-type Si, 235
photoluminescence and chemical bonding in porous silicon layers—dependence on the P concentration in the Si substrate, 248
the luminescence transition in porous silicon: the nature of the electronic states, 261
adsorption-induced modification of spin and recombination centers in porous silicon, 265
dependence of PS photoluminescence on relative humidity, 268
red, green and blue luminescence in porous silicon—a study of excitation spectra, 272
photoluminescence of laser-deposited porous silicon and its correlation with density of electronic states determined by scanning tunnelling microscopy, 279
stability of electroluminescence and photoluminescence of porous silicon, 284
stable and efficient cathodo- and photoluminescence from ultrathin porous silicon layers, 287
silicon needles in porous silicon, 293
electroluminescence from aluminum–porous silicon reverse-biased Schottky diodes formed on the base of highly doped n-type polysilicon, 296
electroluminescence from porous silicon using a conducting polyaniline contact, 299
photo-assisted evolution of the photoluminescence spectrum of porous silicon immersed in hydrofluoric acid, 303
the influence of preparation conditions on the photoluminescence spectra of light-emitting Si prepared by laser pulse irradiation of a-Si:H, 306
visible luminescence from C-containing silicon oxide films, 318

Metallization
stability of electroluminescence and photoluminescence of porous silicon, 284
Multilayers
investigation of different oxidation processes for porous silicon studied by spectroscopic ellipsometry, 36
porous silicon multilayer optical waveguides, 143

Nanostructures
X-ray diffraction studies of porous silicon, 1
photo- and potential-controlled nanoporous silicon formation on n-Si(111): an in-situ FTIR Investigation, 25
mechanism of visible photoluminescence from oxidized silicon and germanium nanocrystallites, 44
investigation of the non-radiative processes in porous silicon, 51
transient laser-induced grating spectroscopy in porous silicon, 55
optical non-linearity and hysteresis in porous silicon, 84
on the structural origin of the photoluminescence in silicon powder produced in PECVD processes, 96
visible photoluminescence from silicon nanocrystals formed in silicon dioxide by ion implantation and thermal processing, 104
correlation between microstructure and photoluminescence of nanocrystalline silicon powder prepared by laser-induced CVD, 108
investigation of the quenching mechanisms of the porous silicon luminescence, 130
a porous silicon light-emitting diode with a high quantum efficiency during pulsed operation, 155
time-resolved electroluminescence of porous silicon, 164
electronic properties of thin Au/nanoporous-Si/n-Si structures, 183
preparation of thin nanoporous silicon layers on n- and p-Si, 200
influence of anodization time and current density on the photoluminescence of porous N–Si, 212
influence of photoluminescence and trapping on the photovoltage at the por-Si/p-Si structure, 216
Auger lineshape analysis of porous silicon: experiment and theory, 244
stability of electroluminescence and photoluminescence of porous silicon, 284
recombination with larger than bandgap energy at centres on the surface of silicon microstructures, 290
silicon needles in porous silicon, 293
Nitridation
thermal nitridation of p-type porous silicon in ammonia, 32

Optical properties
transient laser-induced grating spectroscopy in porous silicon, 55
optical non-linearity and hysteresis in porous silicon, 84
excitation of the porous silicon photoluminescence by a multiphoton vibronic process, 116
porous silicon multilayer optical waveguides, 143
two-dimensional infrared photonic crystal based on macroporous silicon, 151
the influence of the doping level on the optical properties of porous silicon, 231
the dielectric function of some low-dimensional Si and Ge structures, 276
Optical spectroscopy
the dielectric function of porous silicon – how to obtain it and how to use it, 7
photoluminescence dynamics of porous silicon: picoseconds to milliseconds, 58
excitation wavelength dependence of Raman and photoluminescence spectra of porous Si membranes, 73
investigation of photoelectrical properties and carrier transport in porous silicon structures by the transient grating technique, 191
Organic substances
light-emitting and photoconductive diodes fabricated with conjugated polymers, 13
Oxidation
high aspect ratio silicon pillars fabricated by electrochemical etching and oxidation of macroporous silicon, 29
investigation of different oxidation processes for porous silicon studied by spectroscopic ellipsometry, 36
mechanism of visible photoluminescence from oxidized silicon and germanium nanocrystallites, 44
anodic oxidation of p- and p^+-type porous silicon: surface structural transformations and oxide formation, 76
characterization of porous silicon-on-insulator films prepared by anodic oxidation, 147
Oxides
anodic oxidation of p- and p^+-type porous silicon: surface structural transformations and oxide formation, 76

characterization of porous silicon-on-insulator films prepared by anodic oxidation, 147
influence of different metallic contacts on porous silicon electroluminescence, 159

Phase transitions
luminescence and Raman scattering from porous silicon under high hydrostatic pressure: a test for the present models of luminescence, 47
Photoconductivity
light-emitting and photoconductive diodes fabricated with conjugated polymers, 13
Photovoltage
influence of photoluminescence and trapping on the photovoltage at the por-Si/p-Si structure, 216
Polymers
light-emitting and photoconductive diodes fabricated with conjugated polymers, 13
electroluminescence from porous silicon using a conducting polyaniline contact, 299
Porous silicon
structure and non-uniform strain analysis on p-type porous silicon by X-ray reflectometry and X-ray diffraction, 238

Quantum effects
investigation of the quenching mechanisms of the porous silicon luminescence, 130
influence of anodization time and current density on the photoluminescence of porous N–Si, 212
recombination with larger than bandgap energy at centres on the surface of silicon microstructures, 290

Raman scattering
illumination-assisted formation of porous silicon, 21
luminescence and Raman scattering from porous silicon under high hydrostatic pressure: a test for the present models of luminescence, 47
drying of porous silicon: a Raman, electron microscopy, and photoluminescence study, 204
the influence of the doping level on the optical properties of porous silicon, 231

Scanning electron microscopy
preparation of thin nanoporous silicon layers on n- and p-Si, 200
stable and efficient cathodo- and photoluminescence from ultrathin porous silicon layers, 287
Scanning tunnelling microscopy
photoluminescence of laser-deposited porous silicon and its correlation with density of electronic states determined by scanning tunnelling microscopy, 279
Schottky barrier
visible light from aluminum–porous silicon Schottky junctions, 168
Secondary ion mass spectrometry
on the origin of blue luminescence arising from atmospheric impregnation of oxidized porous silicon, 112
Silicon
X-ray diffraction studies of porous silicon, 1
the dielectric function of porous silicon – how to obtain it and how to use it, 7
illumination-assisted formation of porous silicon, 21
high aspect ratio silicon pillars fabricated by electrochemical etching and oxidation of macroporous silicon, 29
thermal nitridation of p-type porous silicon in ammonia, 32
investigation of different oxidation processes for porous silicon studied by spectroscopic ellipsometry, 36
electrical contact to porous silicon by electrodeposition of iron, 40
mechanism of visible photoluminescence from oxidized silicon and germanium nanocrystallites, 44
luminescence and Raman scattering from porous silicon under high hydrostatic pressure: a test for the present models of luminescence, 47
investigation of the non-radiative processes in porous silicon, 51
transient laser-induced grating spectroscopy in porous silicon, 55
photoluminescence dynamics of porous silicon: picoseconds to milliseconds, 58
an in-situ method of monitoring the surface area of porous silicon, 61
bimodal size distribution in p^- porous silicon studied by small angle X-ray scattering, 65
X-ray diffraction investigation of porous silicon superlattices, 69
excitation wavelength dependence of Raman and photoluminescence spectra of porous Si membranes, 73
light scattering from porous silicon, 80
optical non-linearity and hysteresis in porous silicon, 84
photoluminescence studies of light emission from silicon implanted and annealed SiO_2 layers, 88
defects and visible photoluminescence in porous $Si_{1-x}Ge_x$, 92
on the structural origin of the photoluminescence in silicon powder produced in PECVD processes, 96
continuously tunable photoluminescence from Si^+-implanted and thermally annealed SiO_2 films, 100
visible photoluminescence from silicon nanocrystals formed in silicon dioxide by ion implantation and thermal processing, 104
correlation between microstructure and photoluminescence of nanocrystalline silicon powder prepared by laser-induced CVD, 108
excitation of the porous silicon photoluminescence by a multiphoton vibronic process, 116
polarization of porous silicon photoluminescence: alignment and built-in anisotropy, 120
mechanisms of luminescence tuning and quenching in porous silicon, 123
investigation of the quenching mechanisms of the porous silicon luminescence, 130
temperature-dependent photoluminescence in porous amorphous silicon, 134
a novel capacitor technology based on porous silicon, 138
porous silicon multilayer optical waveguides, 143
characterization of porous silicon-on-insulator films prepared by anodic oxidation, 147
two-dimensional infrared photonic crystal based on macroporous silicon, 151
a porous silicon light-emitting diode with a high quantum efficiency during pulsed operation, 155
influence of different metallic contacts on porous silicon electroluminescence, 159
time-resolved electroluminescence of porous silicon, 164
visible light from aluminum–porous silicon Schottky junctions, 168
conduction in porous silicon contacted by a liquid phase, 175
electrical characterization of metal Schottky contacts on luminescent porous silicon, 179
electronic properties of thin Au/nanoporous-Si/n-Si structures, 183
charge transport in porous silicon: considerations for achievement of efficient electroluminescence, 187
investigation of photoelectrical properties and carrier transport in porous silicon structures by the transient grating technique, 191
residual electrolyte as a factor influencing the electrical properties of porous silicon, 195
preparation of thin nanoporous silicon layers on n- and p-Si, 200
drying of porous silicon: a Raman, electron microscopy, and photoluminescence study, 204
effect of light intensity on photoluminescence properties of n-type porous silicon, 208
influence of photoluminescence and trapping on the photovoltage at the por-Si/p-Si structure, 216

about the origin and the mechanisms involved in the cracking of highly porous silicon layers under capillary stresses, 219
characterization of different porous silicon structures by spectroscopic ellipsometry, 223
enhanced light absorption in anodically etched silicon wafers, 228
the influence of the doping level on the optical properties of porous silicon, 231
Auger lineshape analysis of porous silicon: experiment and theory, 244
photoluminescence and chemical bonding in porous silicon layers—dependence on the P concentration in the Si substrate, 248
metallisation of porous silicon by chemical vapour infiltration and deposition, 253
formation of porous silicon on patterned substrates, 257
the luminescence transition in porous silicon: the nature of the electronic states, 261
adsorption-induced modification of spin and recombination centers in porous silicon, 265
dependence of PS photoluminescence on relative humidity, 268
red, green and blue luminescence in porous silicon—a study of excitation spectra, 272
the dielectric function of some low-dimensional Si and Ge structures, 276
photoluminescence of laser-deposited porous silicon and its correlation with density of electronic states determined by scanning tunnelling microscopy, 279
stability of electroluminescence and photoluminescence of porous silicon, 284
stable and efficient cathodo- and photoluminescence from ultrathin porous silicon layers, 287
recombination with larger than bandgap energy at centres on the surface of silicon microstructures, 290
silicon needles in porous silicon, 293
electroluminescence from aluminum–porous silicon reverse-biased Schottky diodes formed on the base of highly doped n-type polysilicon, 296
electroluminescence from porous silicon using a conducting polyaniline contact, 299
photo-assisted evolution of the photoluminescence spectrum of porous silicon immersed in hydrofluoric acid, 303
the influence of preparation conditions on the photoluminescence spectra of light-emitting Si prepared by laser pulse irradiation of a-Si:H, 306
characterization of silicon-implanted SiO_2 layers using positron annihilation spectroscopy, 310
microscopic characterization of microcrystalline silicon thin films, 314

Silicon dioxide
continuously tunable photoluminescence from Si^+-implanted and thermally annealed SiO_2 films, 100
characterization of silicon-implanted SiO_2 layers using positron annihilation spectroscopy, 310

Silicon oxide
observation of (100) surfaces in p-type porous silicon by electron paramagnetic resonance, 241
visible luminescence from C-containing silicon oxide films, 318

Solar cells
enhanced light absorption in anodically etched silicon wafers, 228

Solid electrolyte interface
conduction in porous silicon contacted by a liquid phase, 175

Sputtering
visible luminescence from C-containing silicon oxide films, 318

Stress
about the origin and the mechanisms involved in the cracking of highly porous silicon layers under capillary stresses, 219
structure and non-uniform strain analysis on p-type porous silicon by X-ray reflectometry and X-ray diffraction, 238

Structural properties
bimodal size distribution in p^- porous silicon studied by small angle X-ray scattering, 65
X-ray diffraction investigation of porous silicon superlattices, 69
anodic oxidation of p- and p^+-type porous silicon: surface structural transformations and oxide formation, 76
correlation between microstructure and photoluminescence of nanocrystalline silicon powder prepared by laser-induced CVD, 108
two-dimensional infrared photonic crystal based on macroporous silicon, 151
structure and non-uniform strain analysis on p-type porous silicon by X-ray reflectometry and X-ray diffraction, 238
microscopic characterization of microcrystalline silicon thin films, 314

Superlattices
X-ray diffraction investigation of porous silicon superlattices, 69

Surface and interface states
anodic oxidation of p- and p^+-type porous silicon: surface structural transformations and oxide formation, 76
electronic properties of thin Au/nanoporous-Si/n-Si structures, 183
recombination with larger than bandgap energy at centres on the surface of silicon microstructures, 290

Surface defects
defects and visible photoluminescence in porous $Si_{1-x}Ge_x$, 92

Surface morphology
photo- and potential-controlled nanoporous silicon formation on n-Si(111): an in-situ FTIR Investigation, 25
observation of (100) surfaces in p-type porous silicon by electron paramagnetic resonance, 241

Surface stress
X-ray diffraction studies of porous silicon, 1

Surface tension
drying of porous silicon: a Raman, electron microscopy, and photoluminescence study, 204

Transmission electron microscopy
temperature-dependent photoluminescence in porous amorphous silicon, 134
characterization of silicon-implanted SiO_2 layers using positron annihilation spectroscopy, 310

Wetting
photo-assisted evolution of the photoluminescence spectrum of porous silicon immersed in hydrofluoric acid, 303

X-ray diffraction
X-ray diffraction studies of porous silicon, 1
X-ray diffraction investigation of porous silicon superlattices, 69
structure and non-uniform strain analysis on p-type porous silicon by X-ray reflectometry and X-ray diffraction, 238

X-ray photoelectron spectroscopy (XPS)
illumination-assisted formation of porous silicon, 21
electrical contact to porous silicon by electrodeposition of iron, 40
photoluminescence and chemical bonding in porous silicon layers—dependence on the P concentration in the Si substrate, 248

X-ray scattering
bimodal size distribution in p^- porous silicon studied by small angle X-ray scattering, 65